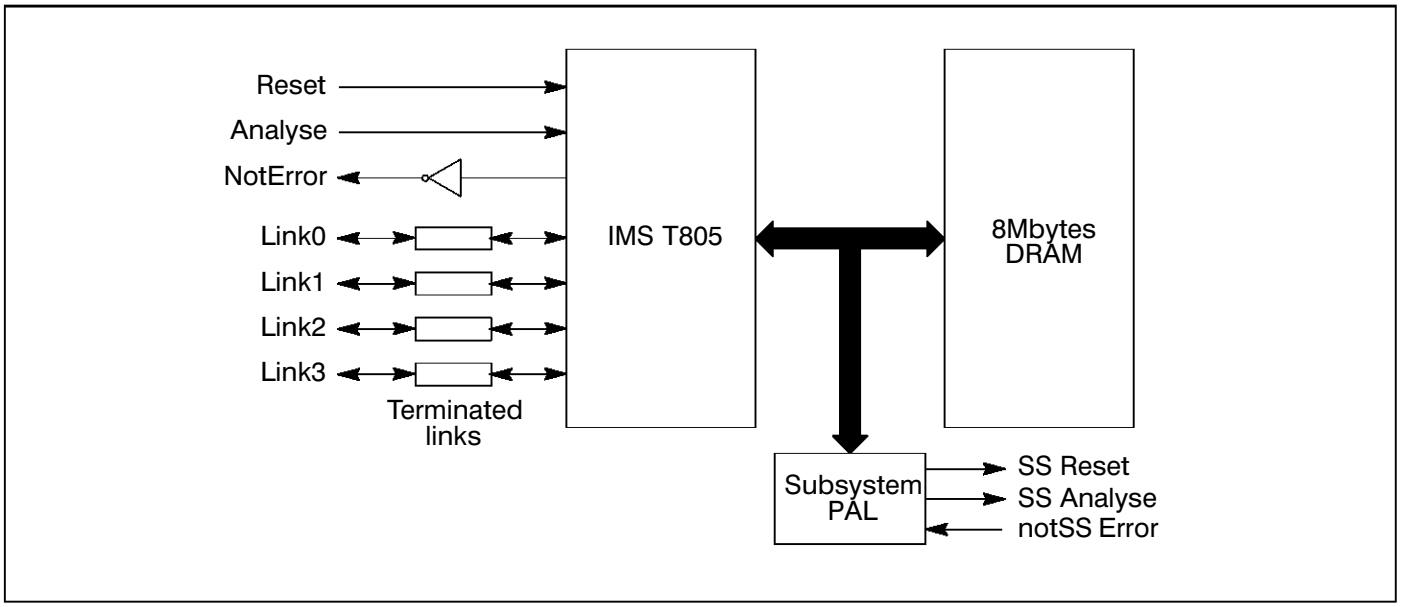
SGS-THOMSON MICROELECTRONICS

IMS B427

8Mbyte Size 2 TRAM



FEATURES

- 25MHz IMS T805 Transputer
- 8 Mbyte of zero wait-state DRAM (120ns memory cycle time)
- Size 2 TRAM
- Communicates via 4 INMOS serial links
- Package has only 16 active pins
- Subsystem control circuitry
- Designed to a published specification (*INMOS Technical Note 29*).

DESCRIPTION

The IMS B427 is a compact size 2 TRAM offering 8Mbytes of 4–cycle DRAM and subsystem controller circuitry.

With a large amount of external memory, the B427 is able to run all of the INMOS development tools. It is ideally suited for applications using large amounts of memory, allowing progams such as simulation and AI evaluation to run quickly and efficiently.

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1.7 Specification

TRAM feature	IMS B427-16	Unit	Notes
Transputer type	T805-25		
Number of transputers	1		
Number of INMOS serial links	4		
Amount of SRAM	None		
SRAM ‘wait -states’	N/A		
Amount of DRAM	8	Mbyte	
DRAM ‘wait -states’	0		
Memory cycle time	120	ns	
Subsystem controller	Yes		
Peripheral circuitry	None		
Parity	No		
Size (TRAM size)	2		
Length	3.66	inch	
Pitch between pins	3.30	inch	
Width	2.15	inch	
Component height above PCB	9.2	mm	
Component height below PCB	3.1	mm	1
Weight	63	g	
Storage temperature	0–70	^{o}C	
Operating temperature	0–50	^{o}C	2
Power supply voltage (VCC)	4.75–5.25	Volt	
Power consumption	4.6	W	3

Table 1.4 IMS B427 specification

Notes

1 This dimension includes the thickness of the PCB.

2 The figure quoted refers to the ambient air temperature.

3 The power consumption is the worst case value obtained when a sample of IMS B427 TRAMs were tested (running a program that utilised all four links and accessed memory simultaneously) at a supply voltage (VCC) of 5.25 V.

1.8 Ordering Information

Description	Order Number
IMS B427 TRAM with IMS T805-25	IMS B427-16

Table 1.5 Ordering information